# **CNB1001**

### Reflective photosensor

#### For contactless SW and object detection

#### Overview

CNB1001 is a small, thin SMD-compatible reflective photosensor consisting of a high efficiency GaAs infrared light emitting diode which is integrated with a high sensitivity Si phototransistor in a single resin package.

#### Features

- Reflow-compatible reflective photosensor
- Ultraminiature, thin type: 2.7 mm × 3.4 mm (height: 1.5 mm)
- Visible light cutoff resin is used

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

F	Symbol	Rating	Unit	
Input (Light emitting diode)	Power dissipation *1	P <sub>D</sub>	75	mW
	Forward current	$I_{\rm F}$	50	mA
	Reverse voltage	V <sub>R</sub> 6		V
Output (Photo transistor)	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	35	V
	Emitter-collector voltage (Base open)	V <sub>ECO</sub>	6	V
	Collector current	I <sub>C</sub>	20	mA
	Collector power dissipation *2	P <sub>C</sub>	75	mW
Operating ambient temperature		T <sub>opr</sub>	-25 to +85	°C
Storage temperature		T <sub>stg</sub>	-40 to +100	°C

Note) \*1: Input power derating ratio is 1.0 mW/°C at  $T_a \ge 25$ °C.

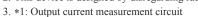
\*2: Output power derating ratio is 1.0 mW/°C at  $T_a \ge 25$ °C.

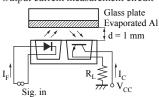
#### Electrical-Optical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

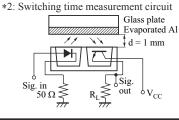
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I <sub>R</sub>	$V_R = 3 V$			10	μΑ
	Forward voltage	V <sub>F</sub>	$I_F = 20 \text{ mA}$		1.2	1.4	V
Output characteristics	Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 20 V$			100	nA
Transfer characteristics	Collector current *1	I <sub>C</sub>	$V_{CC} = 2 V, I_F = 4 mA,$ $R_L = 100 \Omega, d = 1 mm$	23		160	μΑ
	Drain current	ID	$V_{CC} = 2 V, I_F = 4 mA, R_L = 100 \Omega$			100	nA
	Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_F = 20 \text{ mA}, I_C = 0.1 \text{ mA}$			0.4	V
	Rise time *2	t <sub>r</sub>	$V_{\rm CC} = 5 \text{ V}, I_{\rm C} = 0.1 \text{ mA},$		30		μs
	Fall time *2	t <sub>f</sub>	$R_L = 1000\Omega$		40		μs

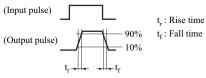
Note) 1. Input and output are handled electrically.

2. This device is designed by disregarding radiation.





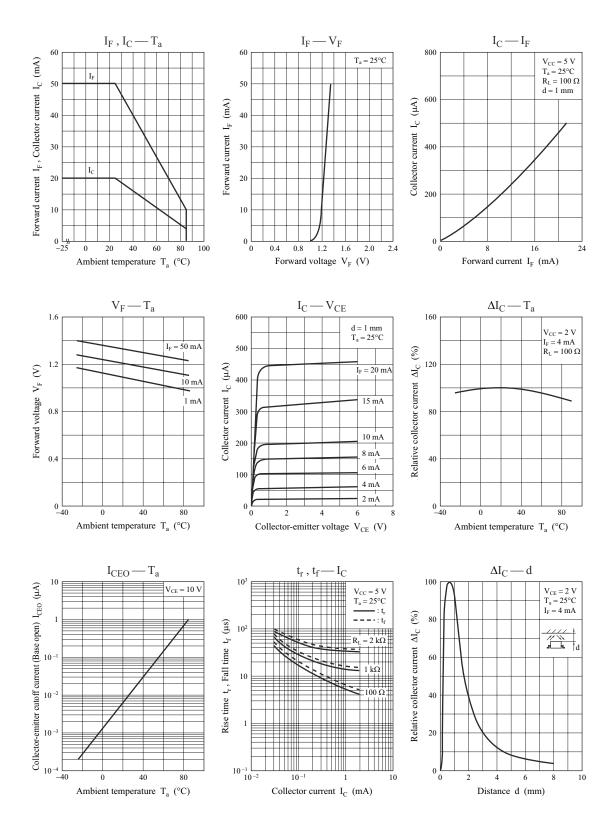




t<sub>f</sub> : Fall time

#### CNB1001

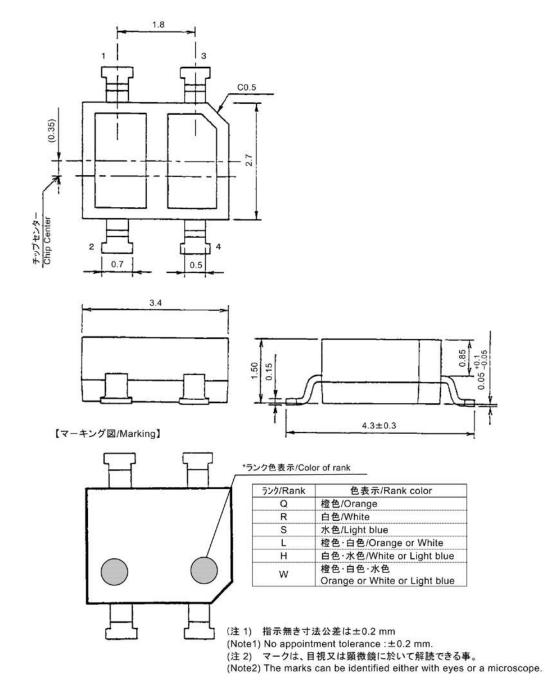
### **Panasonic**



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Package (Unit: mm)

### LSMFRN4G0001



- Pin name
  - 1: Anode
  - 2: Cathode
  - 3: Emitter
  - 4: Collector

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